

N-channel TrenchMOS logic level FET Rev. 3 — 8 February 2011

Product data sheet

Product profile 1.

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- Suitable for logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

1.3 Applications

- 12 V loads
- Automotive systems

- General purpose power switching
- Motors, lamps and solenoids

1.4 Quick reference data

Table 1.	1. Quick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	30	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; see <u>Figure 3</u> ; see <u>Figure 1</u>	<u>[1]</u>	-	-	75	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	300	W
Static cha	aracteristics						
R_{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C		-	2	2.4	mΩ
	resistance	$\label{eq:VGS} \begin{array}{l} V_{GS} = 5 \text{ V}; \text{ I}_{D} = 25 \text{ A}; \\ T_{j} = 25 \text{ °C}; \text{ see } \overline{Figure \ 11}; \\ \text{see } \overline{Figure \ 12} \end{array}$		-	2.4	2.8	mΩ



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Table 1.	Quick reference da	tacontinued				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Avalanch	e ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ \begin{split} I_D &= 75 \text{ A}; \text{V}_{\text{sup}} \leq 30 \text{V}; \\ R_{\text{GS}} &= 50 \Omega; \text{V}_{\text{GS}} = 5 \text{V}; \\ T_{j(\text{init})} &= 25 ^\circ\text{C}; \text{ unclamped} \end{split} $	-	-	2.3	J
Dynamic	characteristics					
Q _{GD}	gate-drain charge	$V_{GS} = 5 V; I_D = 25 A;$ $V_{DS} = 24 V; T_j = 25 °C;$ see Figure 13	-	35	-	nC

[1] Continuous current is limited by package.

Pinning information 2.

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain ^[1]	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

[1] It is not possible to make a connection to pin 2.

Ordering information 3.

Table 3. **Ordering information**

Type number	Package		
	Name	Description	Version
BUK962R8-30B	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

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4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	30	V
V _{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	30	V
V _{GS}	gate-source voltage		-15	15	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 5 V; see <u>Figure 3</u> ;	<u>[1]</u> -	237	А
		see Figure 1	[2] _	75	А
		T_{mb} = 100 °C; V_{GS} = 5 V; see <u>Figure 1</u>	[2] _	75	А
I _{DM}	peak drain current	T _{mb} = 25 °C; pulsed; t _p ≤ 10 μs; see <u>Figure 3</u>	-	950	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	300	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drain	diode				
Is	source current	T _{mb} = 25 °C	[3] _	75	А
			<u>[1]</u> -	237	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	950	А
Avalanche ru	ggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I _D = 75 A; V _{sup} ≤ 30 V; R _{GS} = 50 Ω; V _{GS} = 5 V; T _{j(init)} = 25 °C; unclamped	-	2.3	J

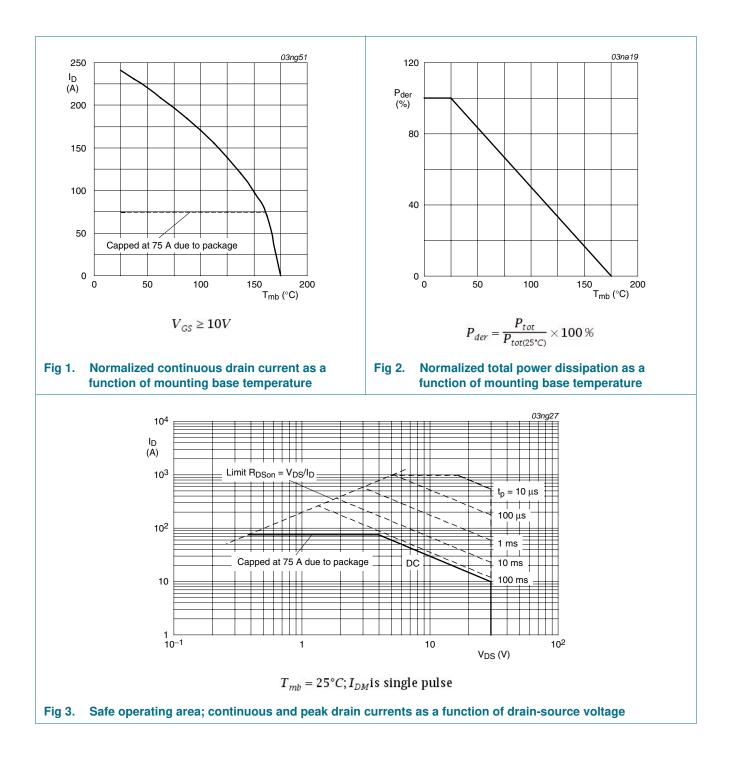
[1] Current is limited by power dissipation chip rating.

[2] Continuous current is limited by package.

[3] Continuous current is limited by package.

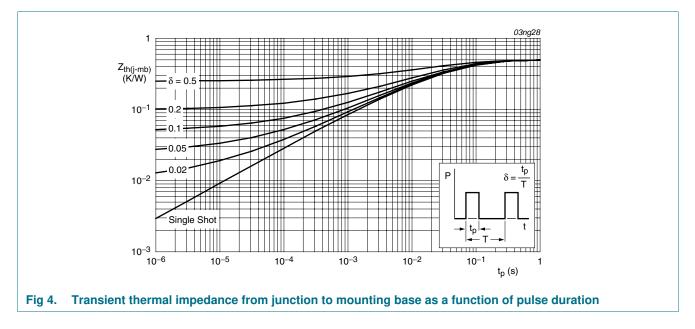
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Thermal characteristics 5.

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	0.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	mounted on a printed-circuit board; minimum footprint	-	50	-	K/W



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6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	octeristics					
V _{(BR)DSS}	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	30	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	27	-	-	V
G.G()	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 10</u>	1.1	1.5	2	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see <u>Figure 10</u>	0.5	-	-	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; see <u>Figure 10</u>	-	-	2.3	V
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	1	μA
		V _{DS} = 30 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
I _{GSS} gate leakage current	V _{GS} = 15 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA	
		$V_{GS} = -15 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
R _{DSon}	drain-source on-state resistance	$V_{GS} = 5 \text{ V}; \text{ I}_{D} = 25 \text{ A}; \text{ T}_{j} = 175 \text{ °C};$ see Figure 11; see Figure 12	-	-	5.3	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C	-	2	2.4	mΩ
	V _{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C	-	-	3	mΩ	
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 11; see Figure 12	-	2.4	2.8	mΩ
Dynamic ch	aracteristics					
Q _{G(tot)}	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 24 \text{ V}; V_{GS} = 5 \text{ V};$	-	89	-	nC
Q _{GS}	gate-source charge	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 13}{13}$	-	22	-	nC
Q _{GD}	gate-drain charge		-	35	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;$	-	7640	10185	pF
C _{oss}	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 14}{\text{Figure } 14}$	-	1600	1920	pF
C _{rss}	reverse transfer capacitance		-	735	1006	pF
d(on)	turn-on delay time	$V_{DS} = 30 \ V; \ R_L = 1.2 \ \Omega; \ V_{GS} = 5 \ V;$	-	71	-	ns
t _r	rise time	$R_{G(ext)} = 10 \ \Omega; T_j = 25 \ ^{\circ}C$	-	222	-	ns
t _{d(off)}	turn-off delay time		-	260	-	ns
t _f	fall time		-	195	-	ns
L _D	internal drain inductance	from upper edge of drain mounting base to centre of die; $T_j = 25 \text{ °C}$	-	2.5	-	nH
		from drain lead 6 mm from package to centre of die; $T_j = 25 \text{ °C}$	-	4.5	-	nH
L _S	internal source inductance	from source lead to source bond pad; $T_j = 25 \text{ °C}$	-	7.5	-	nH

Symbol

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Unit

Max

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Тур

Min

Source-dra	vin diada							
						0.05	1.0	
/ _{SD}	source-drain voltage	$I_S = 40 \text{ A}; V_{GS} = 0$ see <u>Figure 15</u>			-	0.85	1.2	V
rr	reverse recovery time	$I_{\rm S} = 20 \text{ A}; dI_{\rm S}/dt = -$			-	109	-	ns
λr	recovered charge	V _{GS} = -10 V; V _{DS} =	20 V; $I_j = 25 {}^{\circ}C$		-	171	-	nC
300	_	03ng24	5				03ng23	
I _D (A) 10			R _{DSon}					
250 —	V _{GS} = 3.8	3 V	(mΩ)					
		3.6						
200 -			4					
		3.4						
150 —		3.2						
100								
100 -		3	3					
50		2.8						
		2.6						
₀ ک		2.4	2					
0				_		10	15	
0	2 4 6	8 10 V _{DS} (V)	- 0	5		10 V _G	15 S (V)	
0		V _{DS} (V)	0			V _G	_S (V)	
0	2 4 6 $T_j = 25^{\circ}C; t_p = 300\mu$	V _{DS} (V)	0	5 T _j = 25	°C;I _D =	V _G	_S (V)	
	$T_j = 25^{\circ}C; t_p = 300\mu$	V _{DS} (V) <i>1S</i>	0	<i>T</i> _j = 25		V _G = 25A	_S (V)	
Fig 5. Ou		V _{DS} (V) <i>IS</i>	Fig 6. Drain-s		state re	v _G = 25A esistanc	_s (V) e as a f u	
Fig 5. Ou fui	$T_j = 25^{\circ}C; t_p = 300\mu$ utput characteristics: drain	V _{DS} (V) <i>IS</i> a current as a age; typical values	Fig 6. Drain-s	$T_j = 25$	state re	v _G = 25A esistanc	_{s (V)} e as a fu values	
Fig 5. Or fur ^{10−1} ⊨	$T_j = 25^{\circ}C; t_p = 300\mu$ utput characteristics: drain	V _{DS} (V) <i>IS</i> n current as a	Fig 6. Drain-s of gate	$T_j = 25$	state re	v _G = 25A esistanc	_s (V) e as a f u	
Fig 5. Ou fui	$T_j = 25^{\circ}C; t_p = 300\mu$ utput characteristics: drain	V _{DS} (V) <i>IS</i> a current as a age; typical values	Fig 6. Drain-s of gate	$T_j = 25$	state re	v _G = 25A esistanc	_{s (V)} e as a fu values	
Fig 5. Or fur 10 ⁻¹	$T_j = 25^{\circ}C; t_p = 300\mu$ utput characteristics: drain	V _{DS} (V) <i>IS</i> a current as a age; typical values	Fig 6. Drain-s of gate-	$T_j = 25$	state re	v _G = 25A esistanc	_{s (V)} e as a fu values	
Fig 5. Ou fun 10 ⁻¹	$T_j = 25^{\circ}C; t_p = 300\mu$ utput characteristics: drain inction of drain-source volt	V _{DS} (V) <i>IS</i> age; typical values 03ng53	Fig 6. Drain-s of gate	$T_j = 25$	state re	v _G = 25A esistanc	_{s (V)} e as a fu values	
Fig 5. Or fur 10 ⁻¹ ID (A) 10 ⁻²	$T_j = 25^{\circ}C; t_p = 300\mu$ utput characteristics: drain	V _{DS} (V) <i>IS</i> age; typical values 03ng53	Fig 6. Drain-s of gate	$T_j = 25$	state re	v _G = 25A esistanc	_{s (V)} e as a fu values	
Fig 5. Ou fun 10 ⁻¹	$T_j = 25^{\circ}C; t_p = 300\mu$ utput characteristics: drain inction of drain-source volt	V _{DS} (V) <i>IS</i> age; typical values 03ng53	Fig 6. Drain-s of gate grs 0 125 100	$T_j = 25$	state re	v _G = 25A esistanc	_{s (V)} e as a fu values	
Fig 5. Or fur 10 ⁻¹ (A) 10 ⁻²	$T_j = 25^{\circ}C; t_p = 300\mu$ utput characteristics: drain inction of drain-source volt	V _{DS} (V) <i>IS</i> age; typical values 03ng53	Fig 6. Drain-s of gate	$T_j = 25$	state re	v _G = 25A esistanc	_{s (V)} e as a fu values	
Fig 5. Or fur 10 ⁻¹ ID (A) 10 ⁻²	$T_j = 25^{\circ}C; t_p = 300\mu$ utput characteristics: drain inction of drain-source volt	V _{DS} (V) <i>IS</i> age; typical values 03ng53	0 Fig 6. Drain-s of gate	$T_j = 25$	state re	v _G = 25A esistanc	_{s (V)} e as a fu values	
Fig 5. Or fur 10 ⁻¹ (A) 10 ⁻²	$T_j = 25^{\circ}C; t_p = 300\mu$ utput characteristics: drain inction of drain-source volt	V _{DS} (V) <i>IS</i> age; typical values 03ng53	Fig 6. Drain-s of gate grs 0 125 100	$T_j = 25$	state re	v _G = 25A esistanc	_{s (V)} e as a fu values	
Fig 5. Or fur 10 ⁻¹ (A) 10 ⁻² 10 ⁻³	$T_j = 25^{\circ}C; t_p = 300\mu$ utput characteristics: drain inction of drain-source volt	V _{DS} (V) <i>IS</i> age; typical values 03ng53	Fig 6. Drain-s of gate	$T_j = 25$	state re	v _G = 25A esistanc	_{s (V)} e as a fu values	
Fig 5. Or ful 10 ⁻¹ (A) 10 ⁻² 10 ⁻³	$T_j = 25^{\circ}C; t_p = 300\mu$ utput characteristics: drain inction of drain-source volt	V _{DS} (V) <i>IS</i> age; typical values 03ng53	0 Fig 6. Drain-s of gate	$T_j = 25$	state re	v _G = 25A esistanc	_{s (V)} e as a fu values	
Fig 5. Or ful 10 ⁻¹ (A) 10 ⁻² 10 ⁻³ 10 ⁻⁴ 10 ⁻⁵	$T_j = 25^{\circ}C; t_p = 300\mu$ utput characteristics: drain inction of drain-source volt	V _{DS} (V) <i>IS</i> accurrent as a age; typical values 03ng53 / / max	Fig 6. Drain-s of gate (S) 125 100 75 50 25 0	T _j = 25	state re ltage; t	v _G = 25A esistanc typical v	e as a fu ralues 03ng21	unction
Fig 5. Or ful 10 ⁻¹ (A) 10 ⁻² 10 ⁻³	$T_j = 25^{\circ}C; t_p = 300\mu$ utput characteristics: drain inction of drain-source volt	V _{DS} (V) <i>IS</i> age; typical values 03ng53	Fig 6. Drain-s of gate	$T_j = 25$	state re	V _G esistance typical v	_{s (V)} e as a fu values	unction
Fig 5. Or fur 10 ⁻¹ (A) 10 ⁻² 10 ⁻³ 10 ⁻⁴ 10 ⁻⁵	$T_j = 25^{\circ}C; t_p = 300\mu$ utput characteristics: drain inction of drain-source volt	V _{DS} (V)	Fig 6. Drain-s of gate (S) 125 100 75 50 25 0	T _j = 25	40	v _G esistance e	e as a fu values 03ng21	unction
Fig 5. Or full 10^{-1} 10^{-1} (A) 10^{-2} 10^{-3} 10^{-4} 10^{-5} 10^{-6} 0	$T_j = 25^{\circ}C; t_p = 300\mu$ utput characteristics: drain inction of drain-source volt	V _{DS} (V) <i>IS</i> age; typical values	Fig 6. Drain-s of gate	T _j = 25	40	v _G = 25A esistance typical v	e as a fu ralues 03ng21	unction

Table 6. Characteristics ...continued

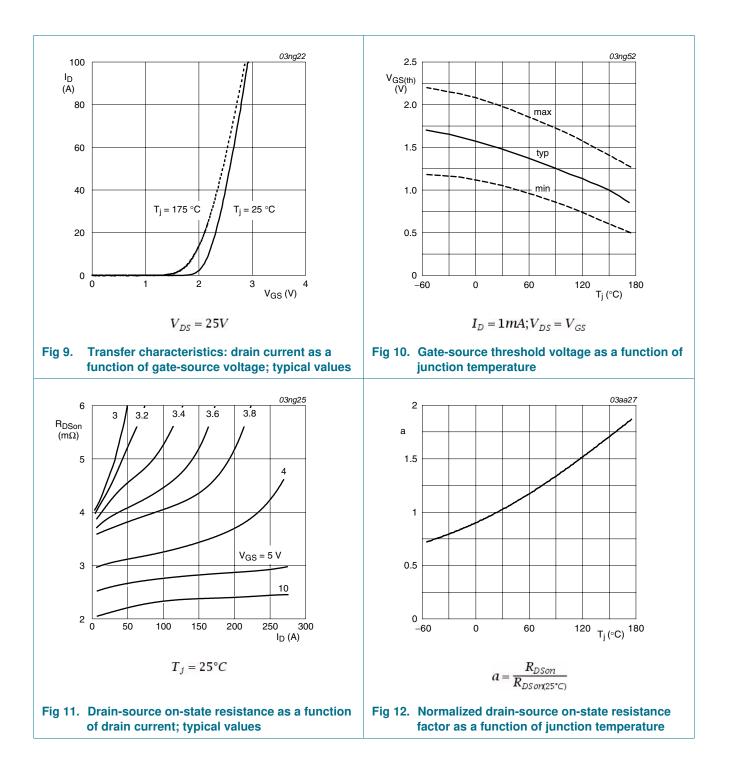
Parameter

Conditions

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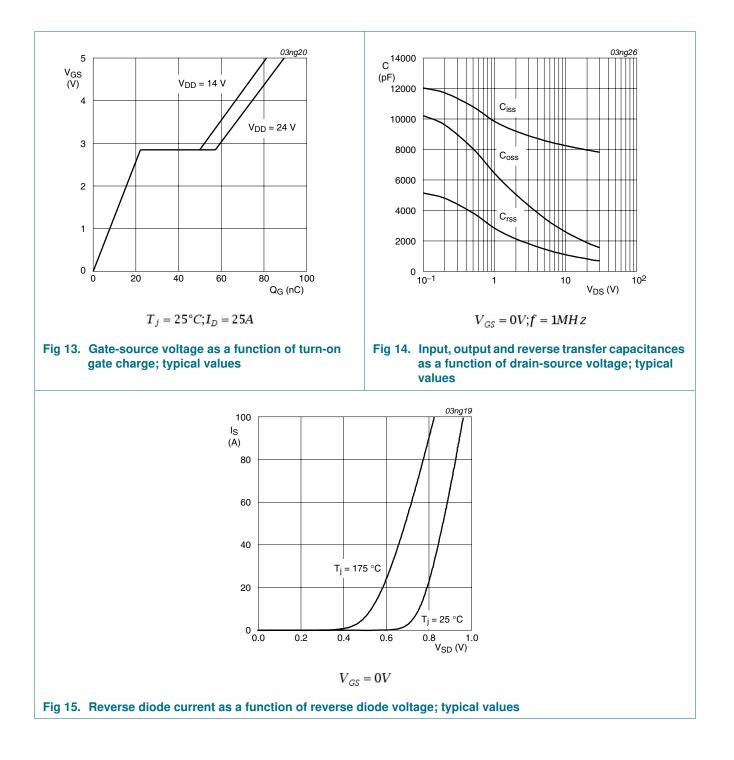
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7. Package outline

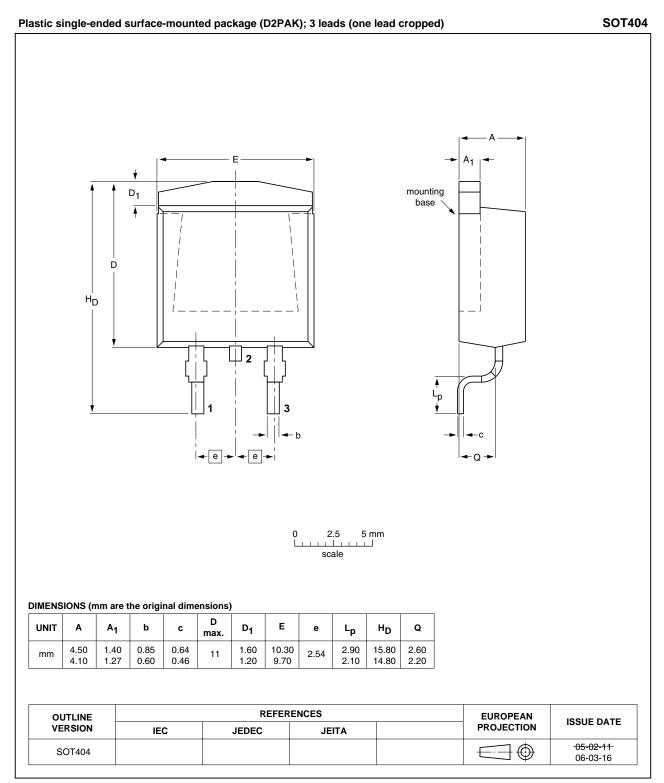


Fig 16. Package outline SOT404 (D2PAK)

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BUK962R8-30B

8. Revision history

Release date	.		
	Data sheet status	Change notice	Supersedes
20110208	Product data sheet	-	BUK95_962R8_30B v.2
		n redesigned to co	omply with the new identity
 Legal texts have 	ave been adapted to the	new company na	me where appropriate.
 Type number 	r BUK962R8-30B separa	ted from data she	et BUK95_962R8_30B v.2.
20021014	Product data	-	BUK95_962R8_30B v.1
	 The format o guidelines of Legal texts h Type number 	 The format of this data sheet has been guidelines of NXP Semiconductors. Legal texts have been adapted to the Type number BUK962R8-30B separation 	 The format of this data sheet has been redesigned to conguidelines of NXP Semiconductors. Legal texts have been adapted to the new company nare Type number BUK962R8-30B separated from data sheet sheet

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9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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